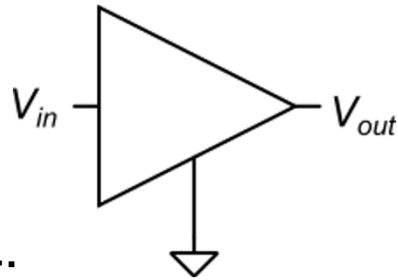
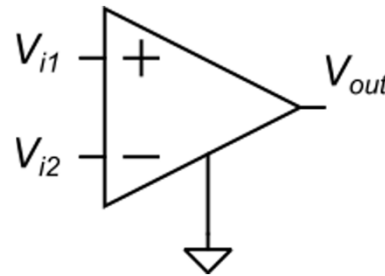


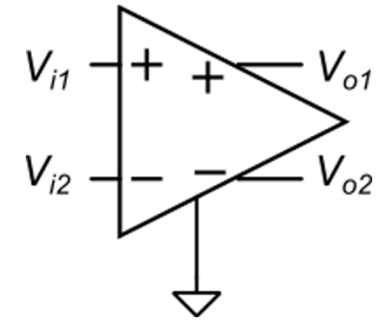
# Voltage amplifiers: number of inputs and outputs



Unipolar:  
single input  
single output (single-ended, S/E)

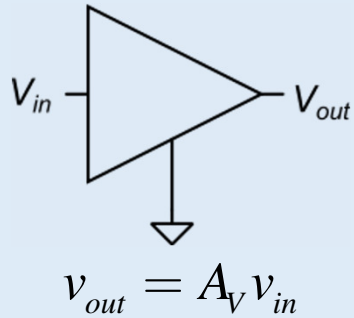


Differential:  
differential input,  
single output (single-ended, S/E)



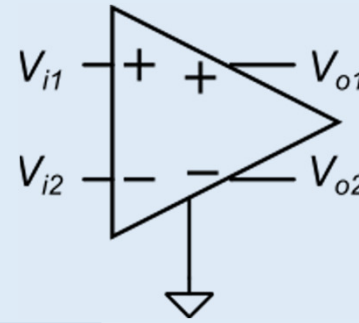
Fully Differential:  
differential input,  
differential output

# Voltage Amplifiers: gains



$$v_{id} = v_{i1} - v_{i2}$$

$$v_{ic} = \frac{v_{i1} + v_{i2}}{2}$$



$$v_{od} = v_{o1} - v_{o2}$$

$$v_{oc} = \frac{v_{o1} + v_{o2}}{2}$$

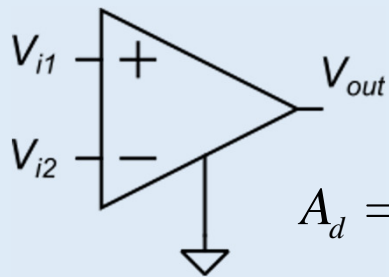
$$A_{dd} = \left. \frac{v_{od}}{v_{id}} \right|_{v_{ic}=0}$$

$$A_{cd} = \left. \frac{v_{od}}{v_{ic}} \right|_{v_{id}=0}$$

$$A_{dc} = \left. \frac{v_{oc}}{v_{id}} \right|_{v_{ic}=0}$$

$$A_{cc} = \left. \frac{v_{oc}}{v_{ic}} \right|_{v_{id}=0}$$

$$CMRR = \left| \frac{A_{dd}}{A_{cd}} \right|$$



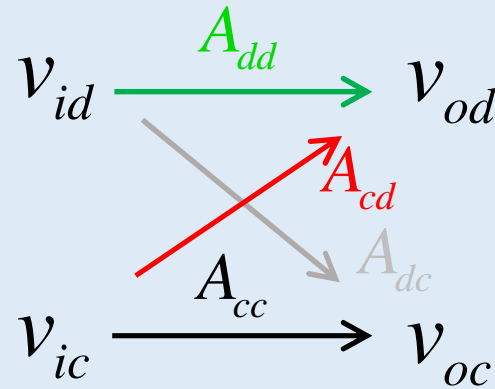
$$A_d = \left. \frac{v_{out}}{v_d} \right|_{v_c=0}$$

$$A_c = \left. \frac{v_{out}}{v_c} \right|_{v_d=0}$$

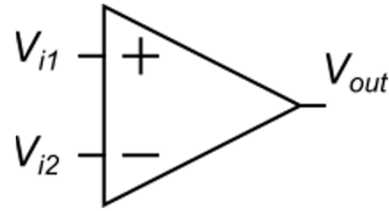
$$v_d = v_{i1} - v_{i2}$$

$$v_c = \frac{v_{i1} + v_{i2}}{2}$$

$$CMRR = \left| \frac{A_d}{A_c} \right|$$



# Differential amplifiers: Ideal behavior and ranges



$$V_{out} = A_d (V_{id} - V_{io})$$

Linear response  
(with input offset voltage)

## Input voltage ranges

**Input differential range**  
(maximum  $V_{ID}$  ( $V_D$ ) to maintain an acceptable input-output linearity)

$$-V_{DMAX} \leq V_D \leq V_{DMAX}$$

**Input common-mode range:**  
Interval of  $V_{IC}$  ( $V_C$ ) values where the amplifier behaves as designed

$$V_{CMIN} \leq V_C \leq V_{CMAX}$$

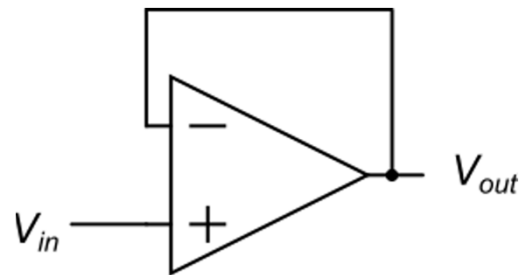
## Output voltage range (Output voltage swing)

$$V_{OMIN} \leq V_{out} \leq V_{OMAX}$$

Outside the output range the amplifier stop working correctly (e.g. the output voltage tends to saturate)

# Differential amplifiers: role of the input common mode range

Example: voltage follower (buffer amplifier)



In the ideal case:

$$V_{io} = 0, A_d \rightarrow \infty$$

We have:

$$V_C = V_{in} \quad \longrightarrow$$
$$V_D \cong 0$$

The voltage follower operates correctly only for  $V_{in}$  within the CM range

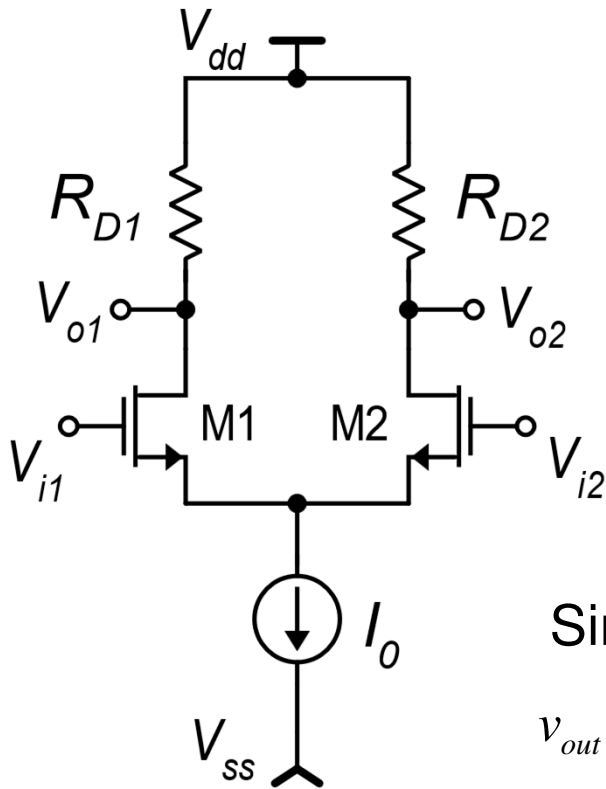
Another condition is clearly that  $V_{out}$  is within the output range

Then the conditions for correct operation are:

$$V_{out} = V_{in} \text{ only for } \begin{cases} V_{CMIN} \leq V_{in} \leq V_{CMAX} \\ V_{OMIN} \leq V_{out} \leq V_{OMAX} \end{cases}$$

$V_{in} \in \text{Input CM range} \cap \text{Output range}$

## Differential amplifier with resistive loads



$$V_{ID} = V_{i1} - V_{i2} \quad V_{OD} = V_{o1} - V_{o2}$$

$$V_{o1} = V_{DD} - R_{D1}I_{D1} \quad V_{o2} = V_{DD} - R_{D2}I_{D2} \quad V_{OD} = R_{D2}I_{D2} - R_{D1}I_{D1}$$

### Small signal analysis

$$v_{o1} = -R_{D1}i_{d1} \quad v_{o2} = -R_{D2}i_{d2} \quad v_{od} = i_{d2}R_{D2} - i_{d1}R_{D1}$$

$$\text{Differential mode: } i_{d1} = \frac{g_m}{2}v_{id} \quad i_{d2} = -\frac{g_m}{2}v_{id}$$

Single-ended case:

$$v_{out} = v_{o1} = -R_{D1} \frac{g_m}{2} v_{id}$$

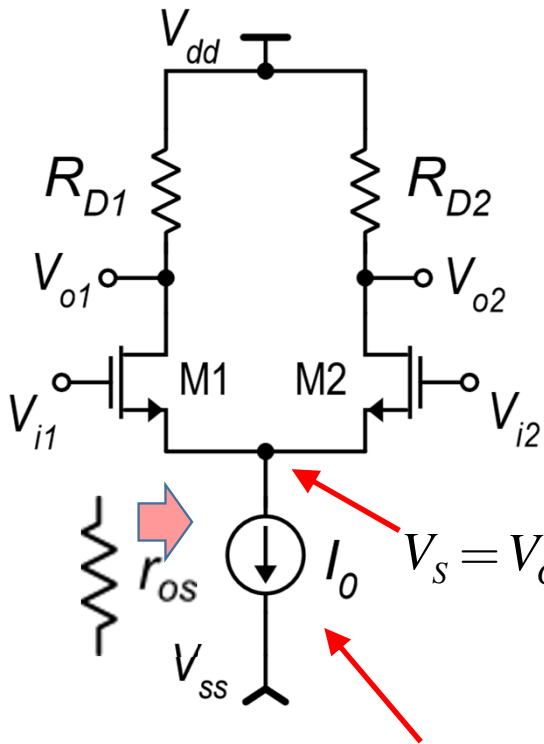
$$A_d = -R_{D1} \frac{g_m}{2}$$

Fully-differential case:

$$v_{out} = v_{od} = -\frac{g_m}{2} (R_{D1} + R_{D2}) v_{id}$$

$$A_{dd} = -g_m \frac{(R_{D1} + R_{D2})}{2}$$

## Common mode Analysis



$$v_{id} = 0 \Rightarrow i_{d1} = i_{d2}$$

$$v_{i1} = v_{i2} = v_c$$

$$i_0 = i_{d1} + i_{d2} = \frac{v_s}{r_{os}}$$

$$v_s = v_{i1} - v_{gs1} = v_c - v_{gs1}$$

$$i_{d1} \cong g_m v_{gs1}$$

$$V_{GS} \cong \text{constant}$$

$$v_{gs1} = \frac{i_{d1}}{g_m}$$

$$v_s = v_c - \frac{i_{d1}}{g_m}$$

$$i_{d1} + i_{d2} = 2i_{d1} = i_0$$

$$i_{d1} = \frac{i_0}{2} = \frac{v_s}{2r_{os}}$$

$$v_s = v_c - \frac{v_s}{2r_{os}g_m}$$

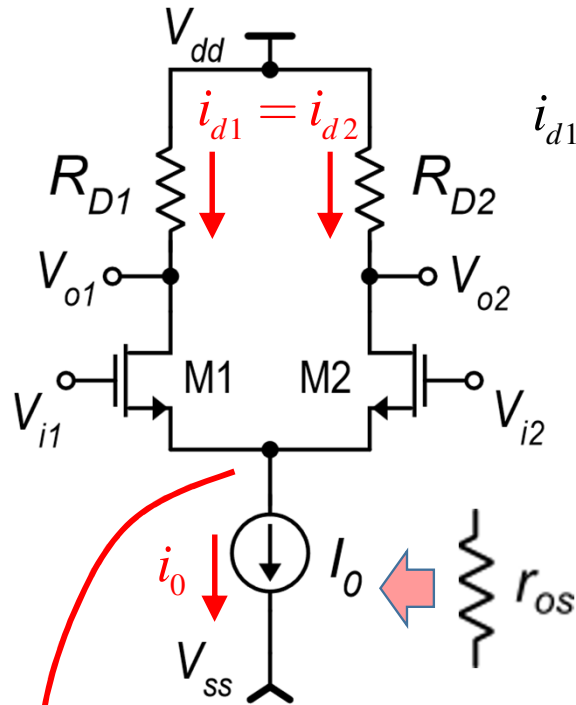
$$v_s = v_c \frac{1}{1 + \frac{1}{2g_m r_{os}}} \cong v_c$$

This, actually, is not an ideal current source. It has a finite output resistance =  $r_{os}$ . If it is implemented by a simple current mirror,  $r_{os} = r_d$  otherwise it can be even higher

The source voltage practically follows the common mode variations.  $V_S$  is  $V_C$  shifted by  $V_{GS}$

# Common mode gain and CMRR

output voltages



$$i_{d1} = i_{d2} \cong \frac{i_o}{2}$$

$$v_{o1} = -R_{D1}i_{d1} \quad v_{o2} = -R_{D2}i_{d2} \quad v_{od} = i_{d2}R_{D2} - i_{d1}R_{D1}$$

## Single-ended case

$$v_{out} = v_{o1} = -R_{D1}i_{d1} \quad v_{out} - R_{D1} \frac{i_o}{2} \cong -R_{D1} \frac{v_c}{2r_{os}}$$

$$A_c = \left. \frac{v_{out}}{v_c} \right|_{v_d=0} \cong -\frac{R_{D1}}{2r_{os}}$$

$$CMRR = \frac{A_d}{A_c} = \frac{g_m R_{D1}}{2} \frac{2r_{os}}{R_{D1}} \quad |A_d|$$

$$v_{i1} = v_{i2} = v_c$$

$$v_s \cong v_c$$

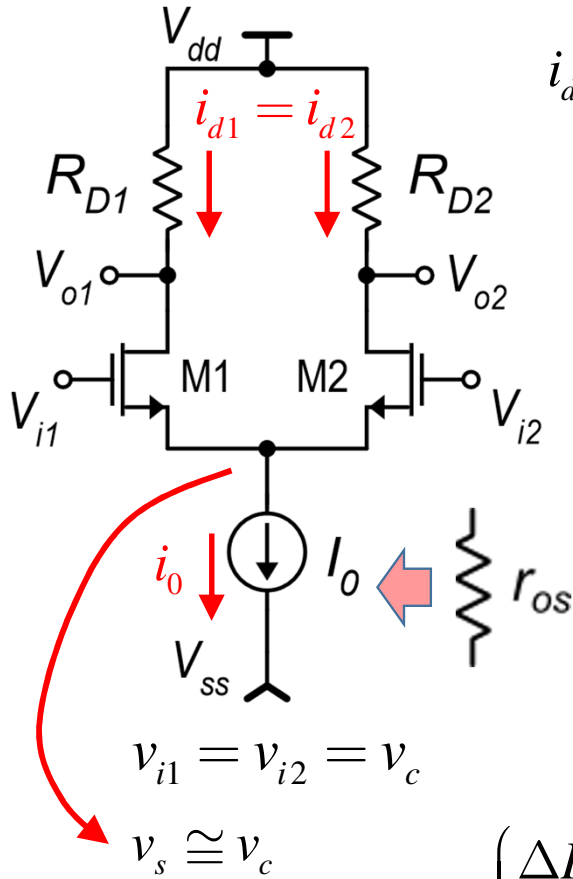
$$i_o = \frac{v_s}{r_{os}} \cong \frac{v_c}{r_{os}}$$

$$CMRR = \left| \frac{A_d}{A_c} \right| = g_m r_{os}$$

Considering that generally  $I_o$  is produced by a simple current mirror,  $r_{os}=r_d$ , then  $CMRR \sim 40$  dB,

**This CMRR is not sufficient for many applications**

# Common mode gain and CMRR



$$i_{d1} = i_{d2} \cong \frac{i_0}{2} \quad v_{o1} = -R_{D1}i_{d1} \quad v_{o2} = -R_{D2}i_{d2} \quad v_{od} = i_{d2}R_{D2} - i_{d1}R_{D1}$$

## Fully differential case

$$v_{out} = v_{od} = \frac{i_0}{2}R_{D2} - \frac{i_0}{2}R_{D1} = \frac{i_0}{2}(R_{D2} - R_{D1})$$

$$v_{out} = \frac{v_c}{2r_{os}}(R_{D2} - R_{D1}) \quad A_{cd} = \frac{v_{od}}{v_{ic}} \Big|_{v_{id}=0} = -\frac{1}{2r_{os}}(R_{D1} - R_{D2})$$

$$CMRR = \left| \frac{A_{dd}}{A_{cd}} \right| = \frac{g_m}{2} \frac{(R_{D1} + R_{D2})}{(R_{D1} - R_{D2})} \frac{2r_{os}}{1} = 2g_m r_{os} \left( \frac{\Delta R_D}{\bar{R}_D} \right)^{-1}$$

$\left( \frac{\Delta R_D}{R_D} \right)$  is a relative matching error  $\sim 0.01$   $\implies \left( \frac{\Delta R_D}{R_D} \right)^{-1} \approx 100$

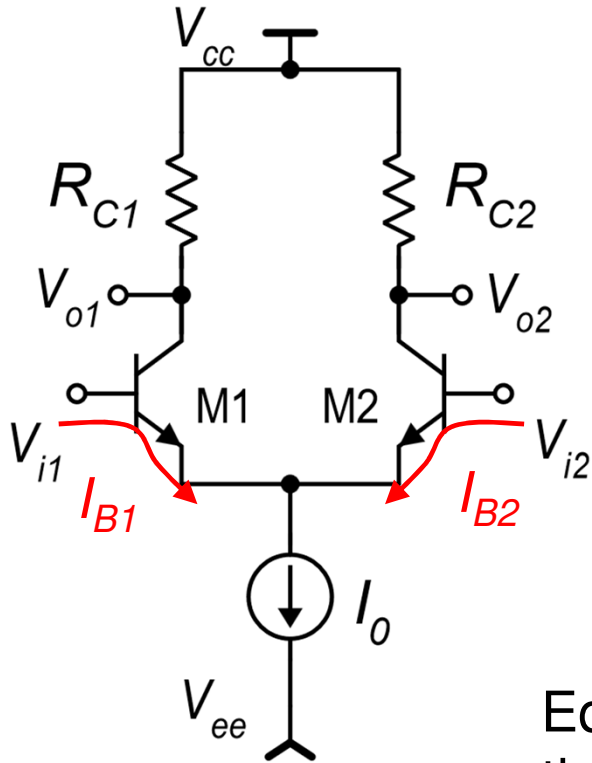
$CMRR \approx 10^4 = 80 \text{ dB}$   
**Adequate for most applications**



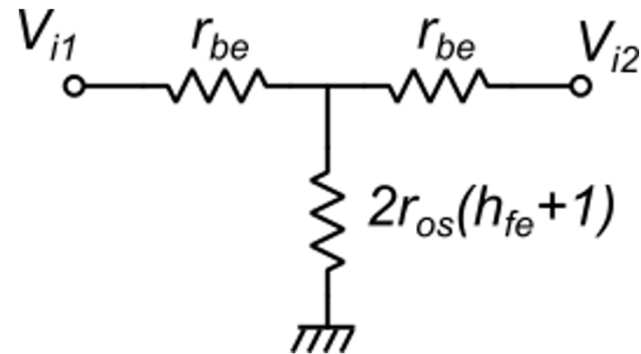
## BJT case

In the case of a BJT differential amplifier, the expressions are exactly the same as for the MOSFET case.

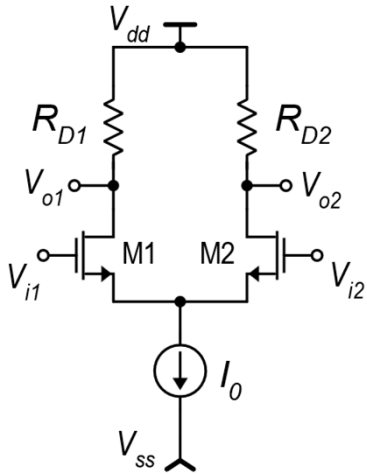
The only important difference is the presence of a base current that is drawn from the voltage sources that provide  $V_{i1}$  and  $V_{i2}$ . In terms of small signal analysis, this base current is the cause of a finite input resistance that may result in an input attenuation if the signal voltage sources ( $V_{i1}$ ,  $V_{i2}$ ) have a significant internal resistance.



Equivalent circuit of the input terminals



## Maximum gain for a given supply voltage



$$\left. \begin{array}{l} \text{single ended} \quad A_d = -R_{D1} \frac{g_m}{2} \quad |A_d| = \frac{g_m R_D}{2} \\ \text{fully-differential} \quad A_{dd} = -g_m \frac{(R_{D1} + R_{D2})}{2} \quad |A_{dd}| = g_m R_D \end{array} \right\} \text{nominal case: } R_{D1} = R_{D2} = R_D$$

$$\text{using: } g_m = \frac{I_D}{V_{TE}} \quad |A_{dd}| = \frac{R_D I_D}{V_{TE}}$$

$$R_D I_D < (V_{DD} - V_{SS})$$

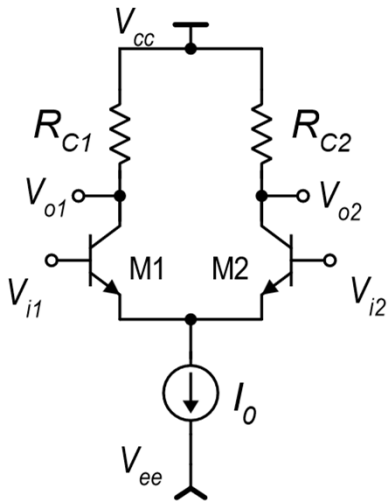
$$|A_{dd}| < \frac{(V_{DD} - V_{SS})}{V_{TE}}$$

$R_D I_D$  is the static voltage drop across resistors  $R_D$ . It cannot exceed the total supply voltage  $V_{DD} - V_{SS}$

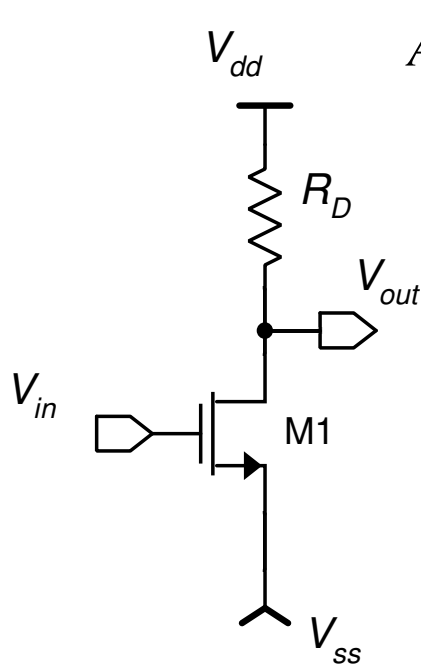
Example:  $V_{TE} = 50 \text{ mV}$ ,  $V_{DD} - V_{SS} = 3 \text{ V}$ :  $|A_{dd}| < 60$

With a BJT:  $V_{TE} = V_T = 25 \text{ mV}$ :  $|A_{dd}| < 120$

To get the highest gain for a given supply voltage it is convenient to bias the MOSFETS with the smallest  $V_{TE}$ .



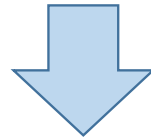
## Unipolar case



$$A = \frac{v_{out}}{v_{in}} \cong -g_m (R_D // r_d)$$

$$|A| \leq g_m R_D$$

This is the same expression as in the case of differential amplifier with resistive load.

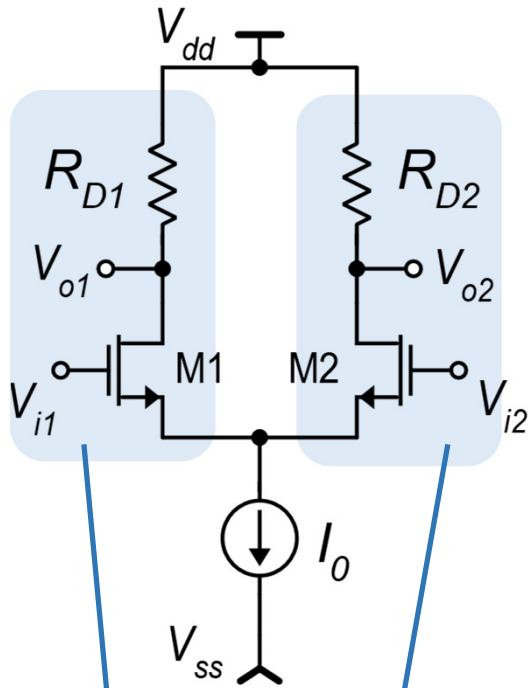


$$|A| < \frac{(V_{DD} - V_{SS})}{V_{TE}}$$

In the case of resistive load, the maximum voltage gain of a unipolar amplifier is subjected to the same limitation as the fully differential amplifier

# Offset voltage of differential amplifiers with resistive load

## MOSFET case - fully-differential - Strong inversion



Nominally identical circuits

$$v_{io} = V_D \Big|_{V_{out}=0}$$

$$V_{out} = V_{o1} - V_{o2}$$

$$V_{GS} = V_t + \sqrt{\frac{2I_D}{\beta}}$$

$$V_{GS} = A + B$$

$$\Delta A = \Delta V_t$$

$$V_D = V_{GS1} - V_{GS2} \triangleq \Delta V_{GS}$$

We can consider the difference of  $V_{GS}$  as the matching error between two nominally identical circuits: M1,  $R_{D1}$  and M2,  $R_{D2}$

$$A = V_t \quad B = \sqrt{\frac{2I_D}{\beta}} = \sqrt{2} \cdot I_D^{\frac{1}{2}} \beta^{-\frac{1}{2}}$$

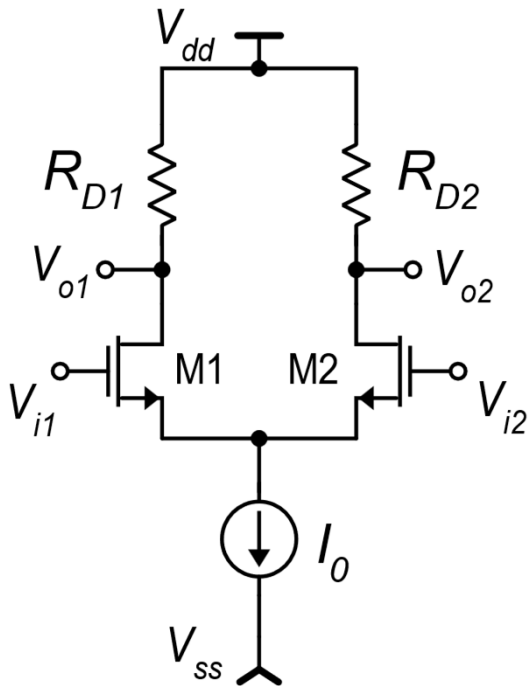
posynomial form

$$\Delta V_{GS} = \Delta A + \Delta B$$

$$\Delta B = B \cdot \frac{\Delta B}{B} = B \cdot \left( \frac{1}{2} \frac{\Delta I_D}{I_D} - \frac{1}{2} \frac{\Delta \beta}{\beta} \right)$$

# Offset voltage of differential amplifiers with resistive load

## MOSFET case - fully-differential



$$V_D = \Delta V_{GS} = \Delta A + \Delta B$$

$$V_{GS} = V_t + \sqrt{\frac{2I_D}{\beta}}$$

A ↓ B

$$\Delta A = \Delta V_t \quad \Delta B = B \cdot \left( \frac{1}{2} \frac{\Delta I_D}{I_D} - \frac{1}{2} \frac{\Delta \beta}{\beta} \right)$$

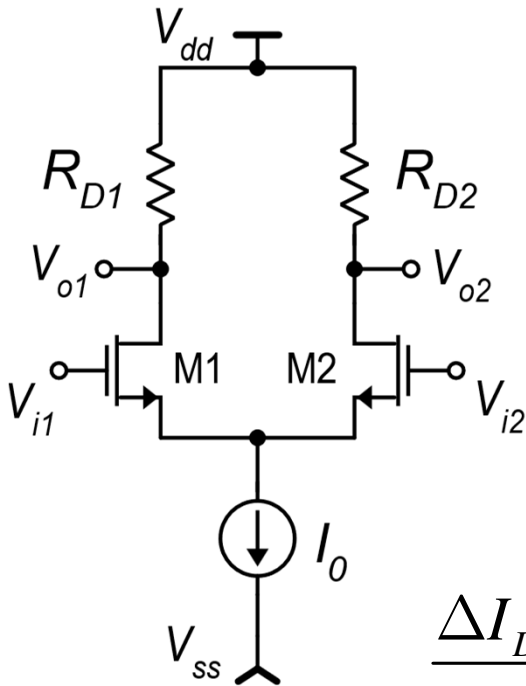
$$V_D = \Delta V_{GS} = \Delta V_t + \sqrt{\frac{2I_D}{\beta}} \cdot \left( \frac{1}{2} \frac{\Delta I_D}{I_D} - \frac{1}{2} \frac{\Delta \beta}{\beta} \right)$$

This is a generic expression of  $V_D$ , corresponding to a generic value of  $\frac{\Delta I_D}{I_D}$

It gives  $V_{io}$  only for the particular  $\frac{\Delta I_D}{I_D}$  value that results in  $V_{out}=0$

# Offset voltage of differential amplifiers with resistive load

## MOSFET case - fully-differential



$$V_{out} = V_{OD} = \underbrace{R_{D2}I_{D2} - R_{D1}I_{D1}}$$

defining:  $Z = R_D I_D$       $\Delta Z = V_{out}$

Imposing  $V_{out}=0$   
is the same as  
imposing  $\Delta Z=0$

$$\Delta Z = \frac{\Delta Z}{Z} Z = \left( \frac{\Delta R_D}{R_D} + \frac{\Delta I_D}{I_D} \right) R_D I_D = 0$$

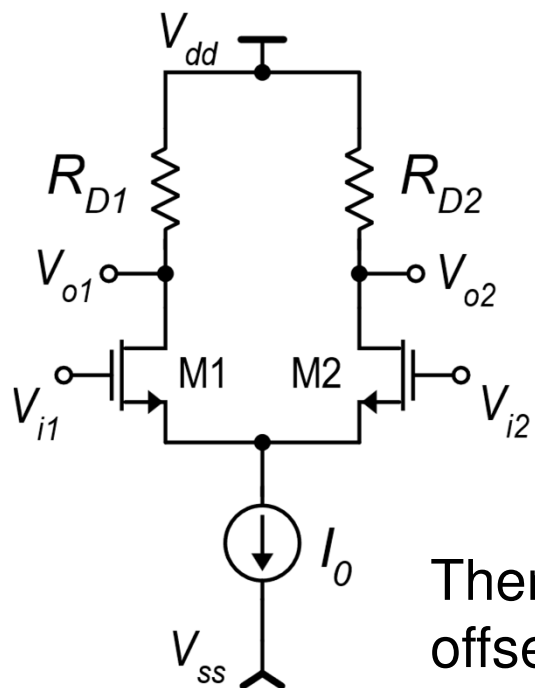
$R_D I_D$  is the nominal  
value and cannot  
be zero

$$\frac{\Delta I_D}{I_D} = -\frac{\Delta R_D}{R_D} \quad \leftarrow \quad = 0 \quad V_D = \Delta V_{GS} = \Delta V_t + \sqrt{\frac{2I_D}{\beta}} \cdot \left( \frac{1}{2} \frac{\Delta I_D}{I_D} - \frac{1}{2} \frac{\Delta \beta}{\beta} \right)$$

$$V_{io} = \Delta V_t + \sqrt{\frac{2I_D}{\beta}} \cdot \left( -\frac{1}{2} \frac{\Delta R_D}{R_D} - \frac{1}{2} \frac{\Delta \beta}{\beta} \right)$$

# Offset voltage of differential amplifiers with resistive load

## MOSFET case - fully-differential



$$V_{io} = \Delta V_t + \sqrt{\frac{2I_D}{\beta}} \cdot \left( -\frac{1}{2} \frac{\Delta R_D}{R_D} - \frac{1}{2} \frac{\Delta \beta}{\beta} \right)$$

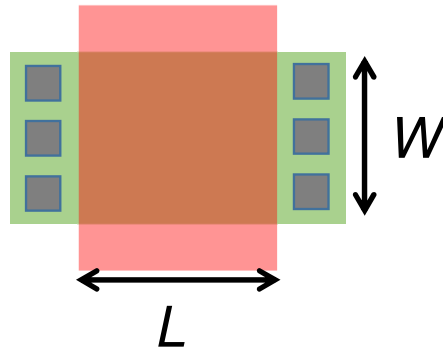
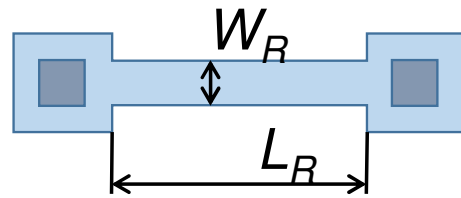
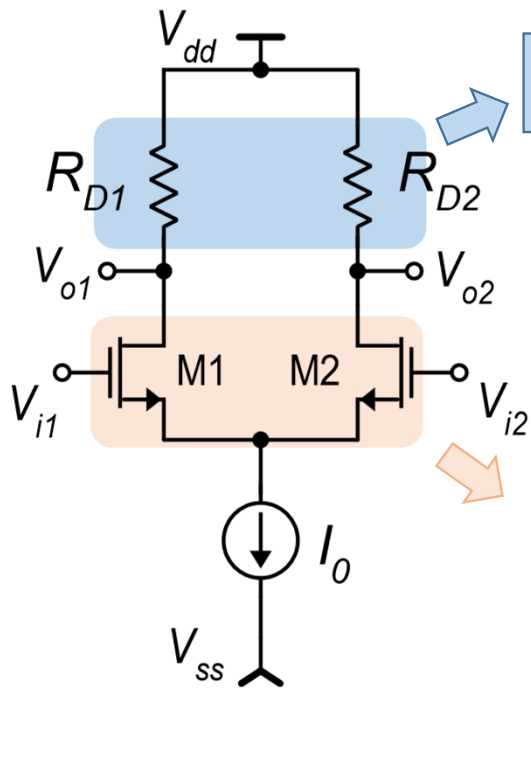
$$V_{io} = \Delta V_t - \frac{(V_{GS} - V_t)}{2} \left( \frac{\Delta R_D}{R_D} + \frac{\Delta \beta}{\beta} \right)$$

$\sqrt{\frac{2I_D}{\beta}} = (V_{GS} - V_t)$

Then, we can calculate the standard deviation of the offset voltage:

$$\sigma_{V_{io}} = \sqrt{\sigma_{V_t}^2 + \left[ \sigma_{\frac{\Delta \beta}{\beta}} \frac{(V_{GS} - V_t)}{2} \right]^2 + \left[ \sigma_{\frac{\Delta R_D}{R_D}} \frac{(V_{GS} - V_t)}{2} \right]^2}$$

# Role of the design parameters



$$\sigma_{V_{io}} = \sqrt{\sigma_{V_t}^2 + \left[ \sigma_{\frac{\Delta\beta}{\beta}} \frac{(V_{GS} - V_t)}{2} \right]^2 + \left[ \sigma_{\frac{\Delta R_D}{R_D}} \frac{(V_{GS} - V_t)}{2} \right]^2}$$

$$\frac{L_R}{W_R} \rightarrow R_D \quad W_R L_R \rightarrow \sigma_{\frac{\Delta R_D}{R_D}} = \frac{C_R}{\sqrt{W_R L_R}}$$

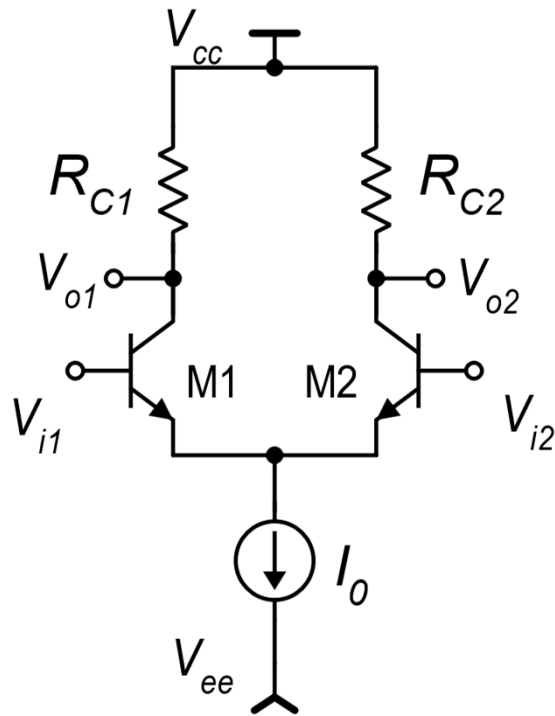
To be made as small as possible, to reduce  $\sigma_{V_{io}}$

$$I_0 \rightarrow (V_{GS} - V_t) \quad W L \rightarrow \begin{cases} \sigma_{V_t} = \frac{C_{vt}}{\sqrt{W L}} \\ \sigma_{\frac{\Delta\beta}{\beta}} = \frac{C_\beta}{\sqrt{W L}} \end{cases}$$

Small offset means large silicon area



## Offset voltage of a BJT differential amplifier with resistor load



$$\underline{v_{io} = V_{id} \big|_{V_{od}=0}} \quad \underline{V_{od} = V_{o1} - V_{o2} = R_{C2}I_{C2} - R_{C1}I_{C1}}$$

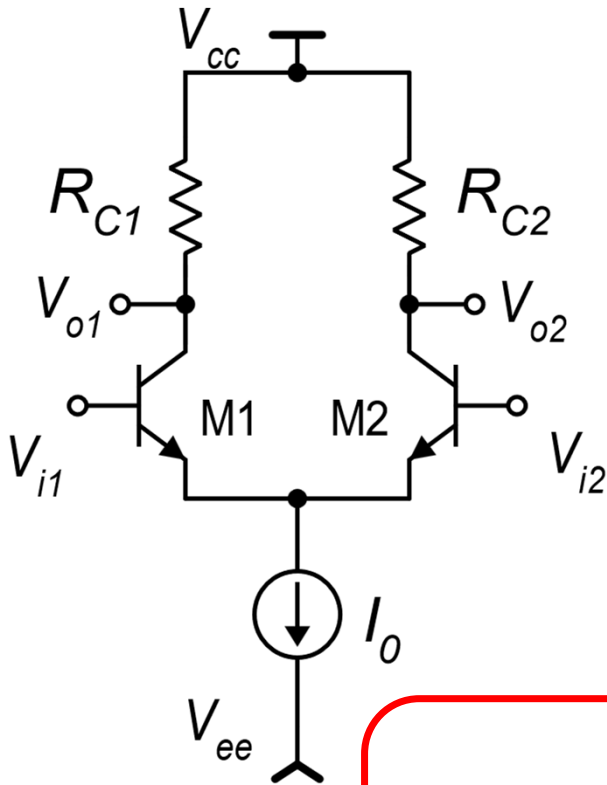
$$V_{id} = V_{i1} - V_{i2} = V_{BE1} - V_{BE2} = \Delta V_{BE}$$

$$V_{BE} = V_T \ln \left( \frac{I_C}{I_S} \right) \quad V_{id} = \Delta V_{BE} = V_T \left( \frac{\Delta I_C}{I_C} - \frac{\Delta I_S}{I_S} \right)$$

$$\underline{V_{od} = 0} \Rightarrow \Delta(R_C I_C) = 0 \Rightarrow \frac{\Delta I_C}{I_C} = -\frac{\Delta R_C}{R_C}$$

$$v_{io} = V_T \left( -\frac{\Delta R_C}{R_C} - \frac{\Delta I_S}{I_S} \right)$$

# Offset voltage of a BJT differential amplifier with resistor load



$$v_{io} = V_T \left( -\frac{\Delta R_C}{R_C} - \frac{\Delta I_S}{I_S} \right)$$

$$\sigma_{vio} = \sqrt{\left( V_T \sigma \frac{\Delta R_C}{R_C} \right)^2 + \left( V_T \sigma \frac{\Delta I_S}{I_S} \right)^2}$$

$$V_T \sigma \frac{\Delta I_S}{I_S} = \sigma_{\Delta V_{BE}^*}$$

$$\sigma_{\frac{\Delta R_C}{R_C}} = \frac{C_R}{\sqrt{W_R L_R}}$$

Minimum size BJT (elemental BJT) of the process

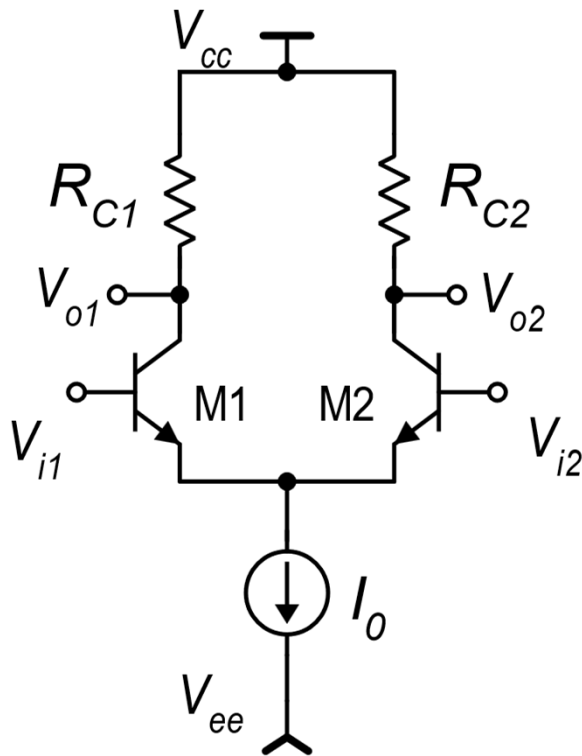
$$\sigma_{\Delta V_{BE-e}^*}$$

$$\sigma_{\Delta V_{BE}^*} = \frac{\sigma_{\Delta V_{BE-e}^*}}{\sqrt{area}}$$

$$\sigma_{vio} = \sqrt{\left( V_T \sigma \frac{\Delta R_C}{R_C} \right)^2 + \sigma_{\Delta V_{BE}^*}^2}$$

Small offset means large silicon area

## Temperature drift of the input offset voltage: BJT case



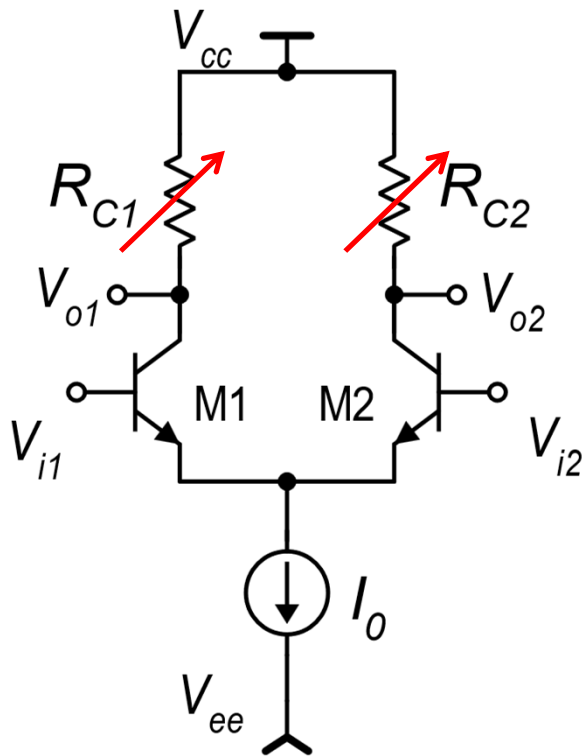
$$v_{io} = \frac{kT}{q} \left( -\frac{\Delta R_C}{R_C} - \frac{\Delta I_S}{I_S} \right)$$

$$\frac{dv_{io}}{dT} = \frac{k}{q} \left( -\frac{\Delta R_C}{R_C} - \frac{\Delta I_S}{I_S} \right)$$

$$\frac{dv_{io}}{dT} = \frac{kT}{q} \left( -\frac{\Delta R_C}{R_C} - \frac{\Delta I_S}{I_S} \right) \frac{1}{T} = \frac{v_{io}}{T}$$

These terms are practically temperature independent (ratios of homogeneous quantities)

## A method to reduce the offset voltage and its drift



$$\frac{dv_{io}}{dT} = \frac{v_{io}}{T}$$

Example:  $v_{io}=1$  mV  
 $T=300$  K

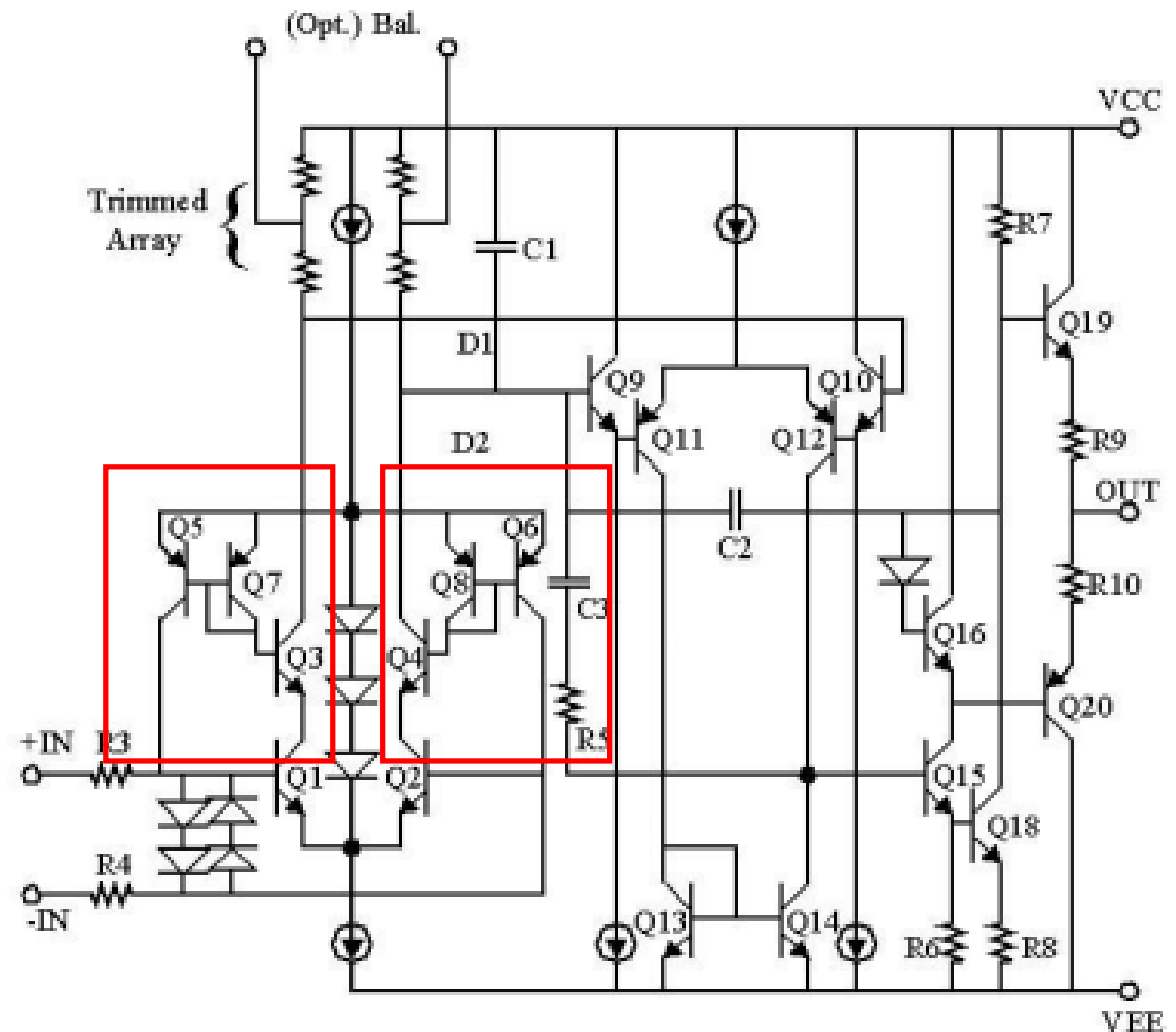
$$\frac{dv_{io}}{dT} = \frac{1.0 \times 10^{-3}}{300} = 3.3 \mu\text{V/K}$$

By trimming the resistors, I can null the offset. In this way, also the temperature drift is nulled.

This is an advantage of the BJT amplifier. Trimming the offset of a MOSFET differential amplifier does not null the drift.

## Example: the OP07

1. Resistors are varied by laser trimming to null the offset
2. In this way, also the offset drift is strongly reduced
3. The base currents of the input devices (Q1, Q2) are reproduced by Q3 and Q4 and than fed back to the input terminals by mirrors Q8, Q6 and Q7, Q5. This approach allows to reduce the input bias currents.



# OP07 vs $\mu$ A741

OP07

Table 1.

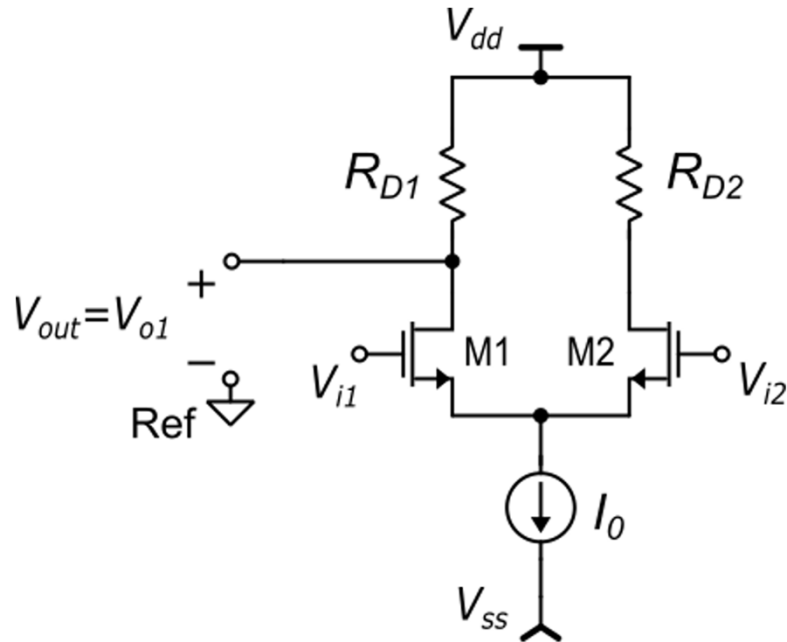
Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
INPUT CHARACTERISTICS							
$T_A = 25^\circ\text{C}$							
Input Offset Voltage <sup>1</sup>	$V_{OS}$	The OP07 has a much better offset than the $\mu$ A 741, whose first stage has not restive loads		30	75	$\mu\text{V}$	
Long-Term $V_{OS}$ Stability <sup>2</sup>	$V_{OS}/\text{Time}$		0.3	1.5	$\mu\text{V}/\text{Month}$		
Input Offset Current	$I_{OS}$		0.5	3.8	nA		
Input Bias Current	$I_B$		$\pm 1.2$	$\pm 4.0$	nA		
$0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$							
Input Offset Voltage <sup>1</sup>	$V_{OS}$		45	130	$\mu\text{V}$		
Voltage Drift Without External Trim <sup>4</sup>	$TCV_{OS}$		0.3	1.3	$\mu\text{V}/^\circ\text{C}$		
Voltage Drift with External Trim <sup>3</sup>	$TCV_{OSN}$	$R_P = 20\text{ k}\Omega$	0.3	1.3	$\mu\text{V}/^\circ\text{C}$		

$\mu$ A741

at specified virtual junction temperature,  $V_{CC\pm} = \pm 15\text{ V}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS <sup>(1)</sup>		MIN	TYP	MAX	UNIT
$V_{IO}$	Input offset voltage	$V_O = 0$	25°C		1	6	mV
			Full range			7.5	
$\Delta V_{IO(\text{adj})}$	Offset voltage adjust range	$V_O = 0$	25°C		$\pm 15$		mV
$I_{IO}$	Input offset current	$V_O = 0$	25°C		20	200	nA
			Full range			300	
$I_{IB}$	Input bias current	$V_O = 0$	25°C		80	500	nA
			Full range			800	

How is the amplifier offset when the single ended option is chosen?



$$V_{out} = V_{O1} = V_{dd} - \underline{\underline{R_1 I_{D1}}}$$

Single ended (S/E): device parameters do not appear as differences: the output voltage is affected mainly by global errors

The single ended case is subjected to a much larger offset!

Compare with the fully-differential case:  
the output voltage depends only on  
matching differences

$$V_{od} = R_{D2} I_{D2} - R_{D1} I_{D1}$$